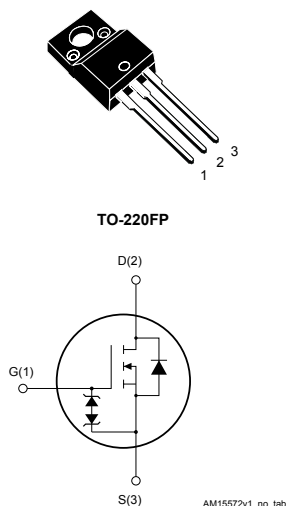


N-channel 600 V, 0.55 Ω typ., 7.5 A MDmesh M2 Power MOSFET in a TO-220FP package



Features

Order code	V_{DS} at $T_{Jmax.}$	$R_{DS(on)}$ max.	I_D
STF10N60M2	650 V	0.60 Ω	7.5 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.



Product status link

[STF10N60M2](#)

Product summary

Order code	STF10N60M2
Marking	10N60M2
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	7.5	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.9	
$I_{DM}^{(2)}$	Drain current (pulsed)	30	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	
$V_{ISO}^{(5)}$	Insulation withstand voltage (RMS) from all three leads to external heat sink	2500	V
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Limited by package.
2. Pulse limited by safe operating area.
3. $I_{SD} \leq 7.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$; $V_{DD} = 400\text{ V}$
4. $V_{DS} \leq 480\text{ V}$.
5. $t = 1\text{ s}$; $T_C = 25\text{ }^\circ\text{C}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	5	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	1.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ

1. Pulse width limited by T_{jmax} .
2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 600 V			1	μA
		V _{GS} = 0 V, V _{DS} = 600 V, T _{case} = 125 °C ⁽¹⁾			100	
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V			±10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 3 A		0.55	0.60	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V	-	400	-	pF
C _{oss}	Output capacitance		-	22	-	
C _{rss}	Reverse transfer capacitance		-	0.84	-	
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V _{DS} = 0 to 480 V, V _{GS} = 0 V	-	83	-	pF
R _G	Intrinsic gate resistance	f = 1 MHz, I _D = 0 A	-	6.4	-	Ω
Q _g	Total gate charge	V _{DD} = 480 V, I _D = 7.5 A, V _{GS} = 0 to 10 V (see) Figure 14. Test circuit for gate charge behavior	-	13.5	-	nC
Q _{gs}	Gate-source charge		-	2.1	-	
Q _{gd}	Gate-drain charge		-	7.2	-	

1. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 3.75 A R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	8.8	-	ns
t _r	Rise time		-	8	-	
t _{d(off)}	Turn-off delay time		-	32.5	-	
t _f	Fall time		-	13.2	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		7.5	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		30	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 7.5\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 7.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see) Figure 15. Test circuit for inductive load switching and diode recovery times	-	270		ns
Q_{rr}	Reverse recovery charge		-	2		μC
I_{RRM}	Reverse recovery current		-	14.4		A
t_{rr}	Reverse recovery time	$I_{SD} = 7.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see) Figure 15. Test circuit for inductive load switching and diode recovery times	-	376		ns
Q_{rr}	Reverse recovery charge		-	2.8		μC
I_{RRM}	Reverse recovery current		-	15		A

1. Limited by package.
2. Pulse width is limited by safe operating area.
3. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics curves

Figure 1. Safe operating area

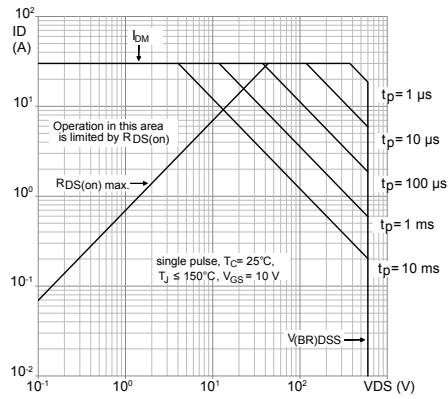


Figure 2. Maximum transient thermal impedance

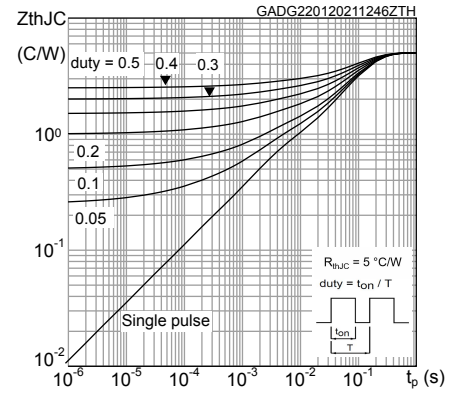


Figure 3. Output characteristics

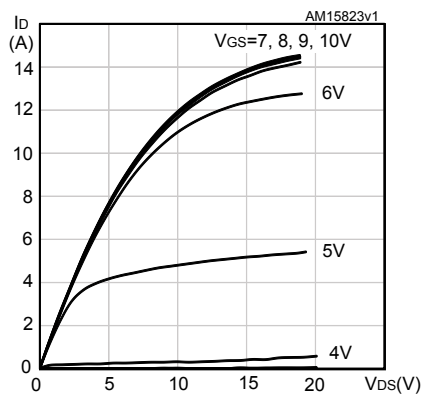


Figure 4. Transfer characteristics

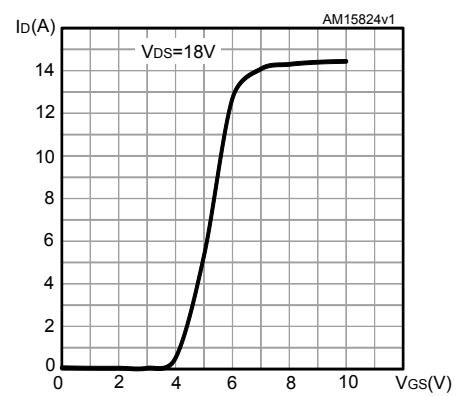


Figure 5. Gate charge vs gate-source voltage

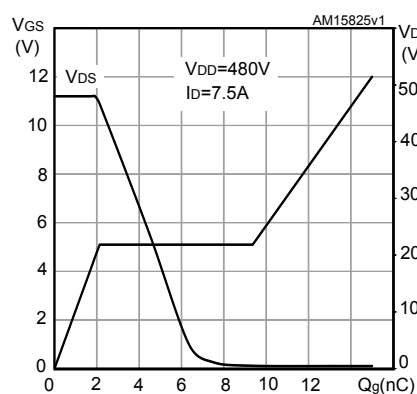


Figure 6. Static drain-source on-resistance

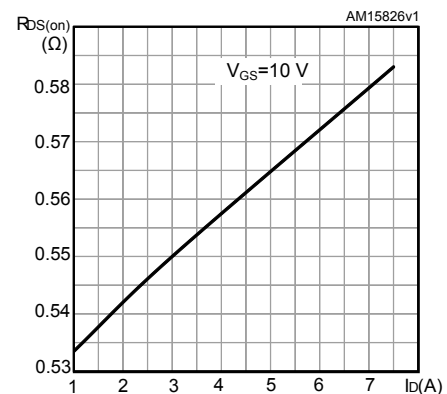


Figure 7. Capacitance variations

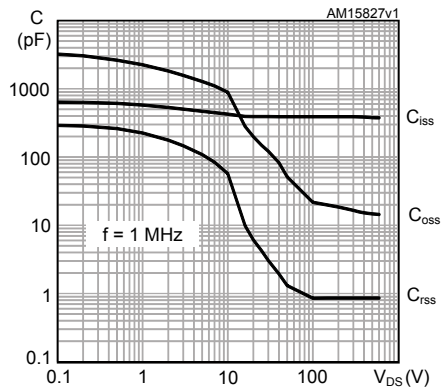


Figure 8. Normalized gate threshold voltage vs temperature

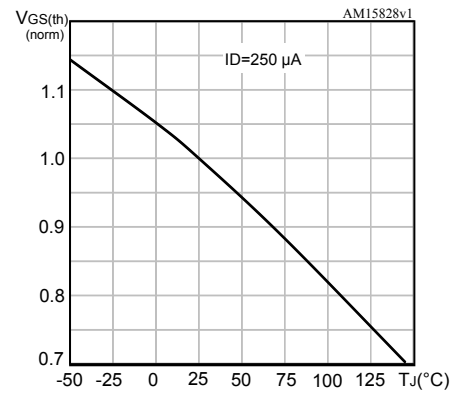


Figure 9. Normalized on-resistance vs temperature

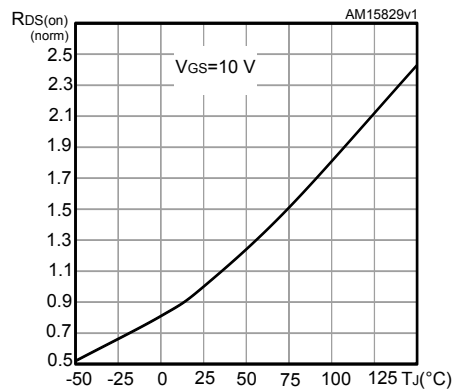


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

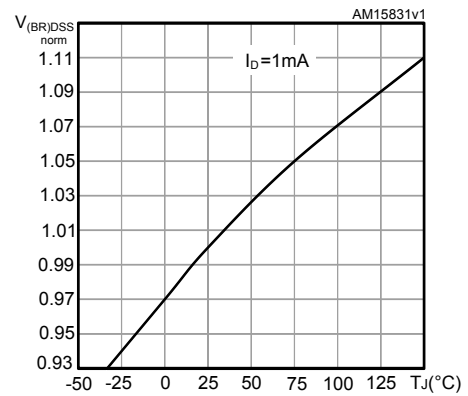


Figure 11. Source-drain diode forward characteristics

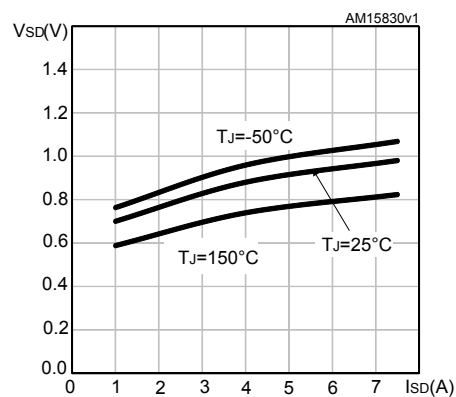
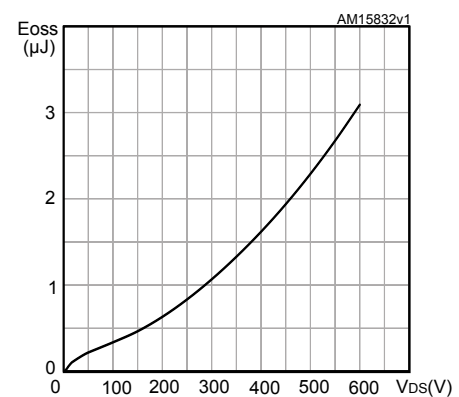
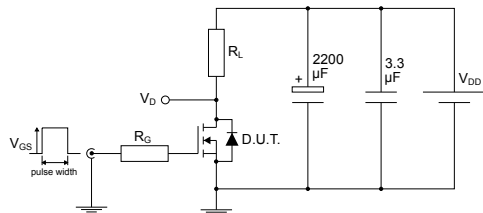


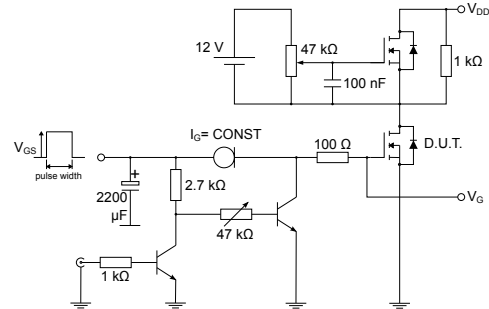
Figure 12. Output capacitance stored energy



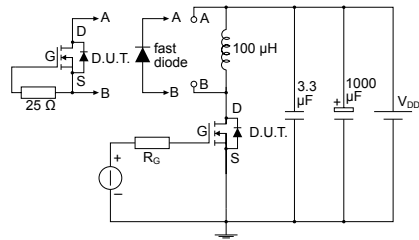
3 Test circuits

Figure 13. Test circuit for resistive load switching times


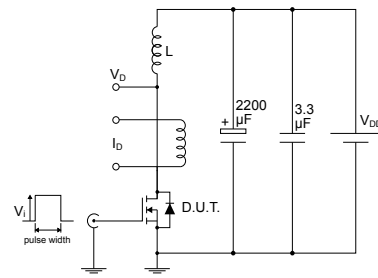
AM01468v1

Figure 14. Test circuit for gate charge behavior


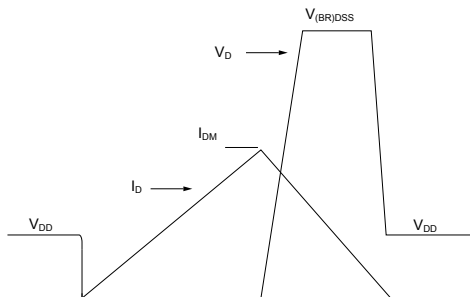
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Figure 15. Test circuit for inductive load switching and diode recovery times


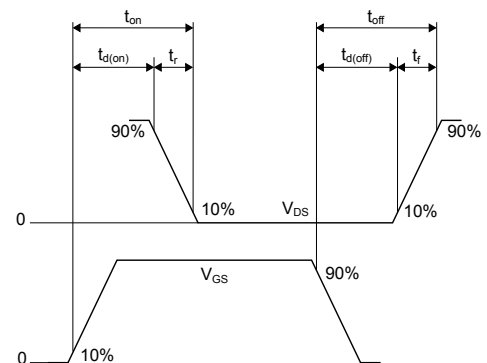
AM01470v1

Figure 16. Unclamped inductive load test circuit


AM01471v1

Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


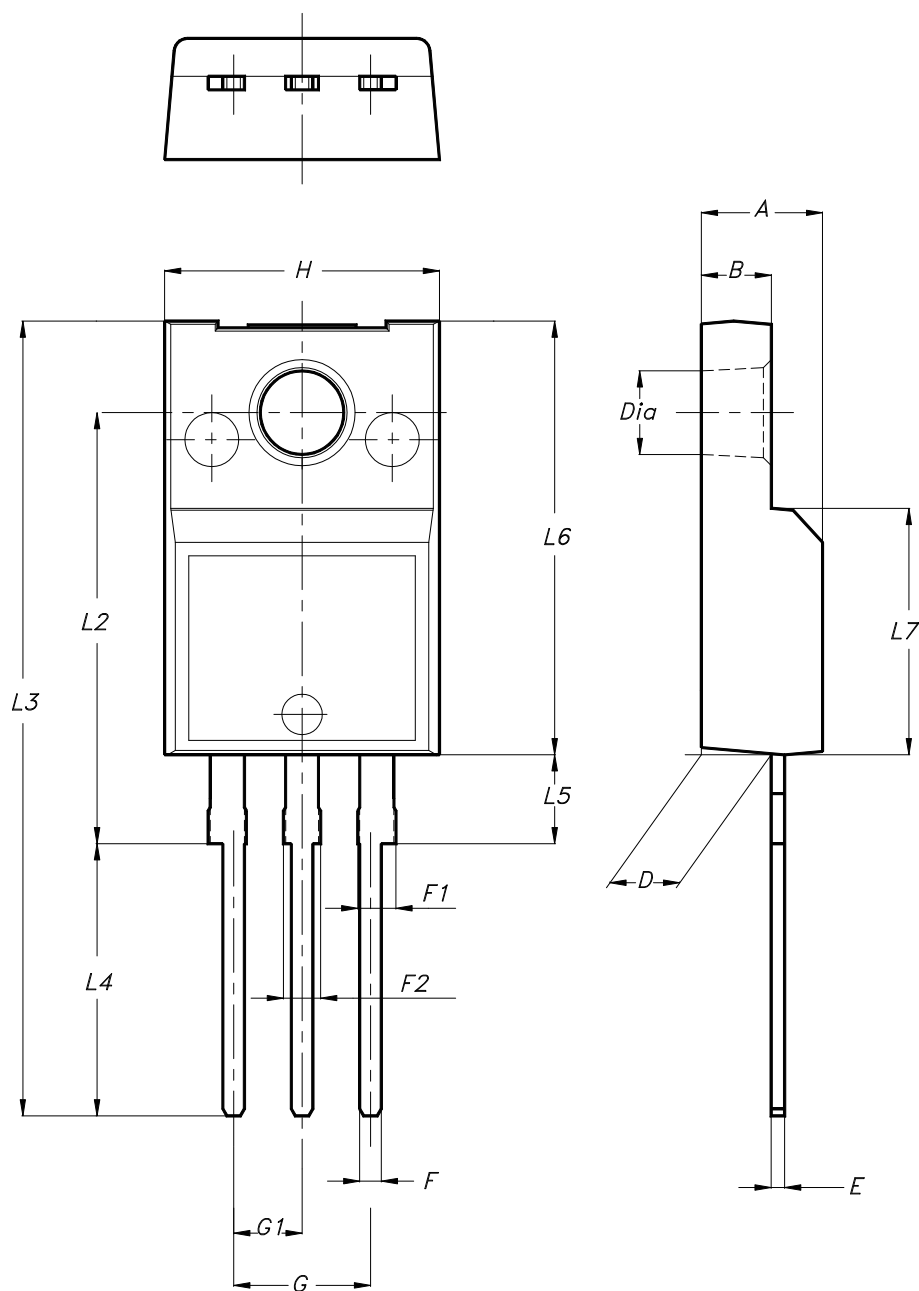
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 19. TO-220FP package outline



7012510_Rev_13_B

Table 8. TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. Document revision history

Date	Revision	Changes
29-May-2013	1	First release.
14-Oct-2013	2	Modified: R_G value in <i>Table 6</i> Minor text changes
06-Dec-2013	3	Added: I ² PAKFP package – Modified: title – Modified: $R_{DS(on)}$ typical values in <i>Table 5</i> – Modified: R_G value in <i>Table 6</i> – Modified: <i>Figure 7</i> and I_D value in <i>Figure 10</i> – Added: <i>Table 10</i> , and <i>Figure 21</i> – Minor text changes
09-Mar-2017	4	The part number STF10N60M2 has been moved to a separate datasheet and this document has been updated accordingly. Updated the title and the description in cover page. Updated <i>Table 3. Avalanche characteristics</i> . Minor text changes.
01-Feb-2021	5	Updated <i>Figure 1</i> and <i>Figure 2</i> . Minor text changes.

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